



ATP302 — P-Channel Silicon MOSFET

General-Purpose Switching Device Applications

Features

- Avalanche resistance guarantee.
- Halogen free compliance.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V _{DSS}		-60	V
Gate-to-Source Voltage	V _{GSS}		±20	V
Drain Current (DC)	I _D		-70	A
Drain Current (Pulse)	I _{DP}	PW≤10μs, duty cycle≤1%	-280	A
Allowable Power Dissipation	P _D	Tc=25°C	70	W
Channel Temperature	T _{ch}		150	°C
Storage Temperature	T _{stg}		-55 to +150	°C
Avalanche Energy (Single Pulse) *1	E _{AS}		197	mJ
Avalanche Current *2	I _{AV}		-42	A

Note : *1 V_{DD}=-36V, L=100μH, I_{AV}=-42A

*2 L≤100μH, Single pulse

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	V(BR)DSS	I _D =-1mA, V _{GS} =0V	-60			V
Zero-Gate Voltage Drain Current	I _{DSS}	V _{DS} =-60V, V _{GS} =0V			-10	μA
Gate-to-Source Leakage Current	I _{GSS}	V _{GS} =±16V, V _{DS} =0V			±10	μA
Cutoff Voltage	V _{GS(off)}	V _{DS} =-10V, I _D =-1mA	-1.2		-2.6	V
Forward Transfer Admittance	y _{fs}	V _{DS} =-10V, I _D =-35A		75		S

Marking : ATP302

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ATP302

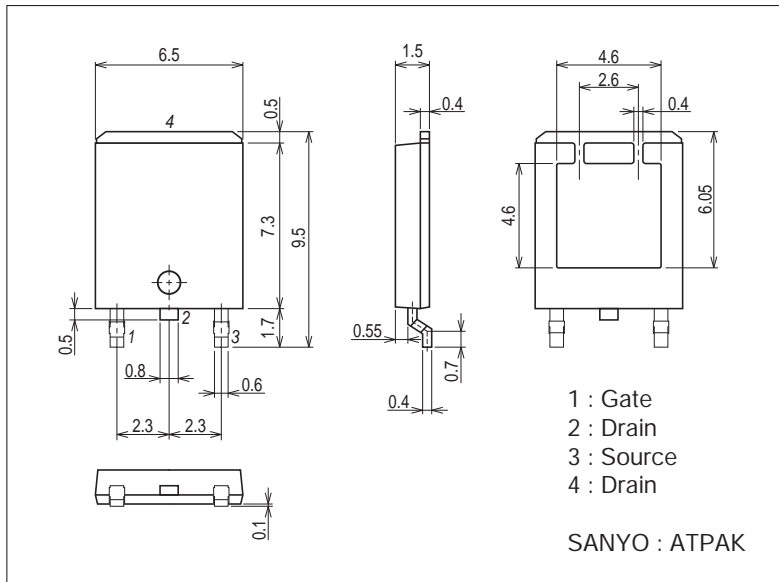
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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Static Drain-to-Source On-State Resistance	$R_{DS(on)1}$	$I_D = -35A, V_{GS} = -10V$		10	13	$m\Omega$
	$R_{DS(on)2}$	$I_D = -35A, V_{GS} = -4.5V$		13	18	$m\Omega$
Input Capacitance	C_{iss}	$V_{DS} = -20V, f = 1MHz$		5400		μF
Output Capacitance	C_{oss}	$V_{DS} = -20V, f = 1MHz$		500		μF
Reverse Transfer Capacitance	C_{rss}	$V_{DS} = -20V, f = 1MHz$		370		μF
Turn-ON Delay Time	$t_{d(on)}$	See specified Test Circuit.		35		ns
Rise Time	t_r	See specified Test Circuit.		430		ns
Turn-OFF Delay Time	$t_{d(off)}$	See specified Test Circuit.		420		ns
Fall Time	t_f	See specified Test Circuit.		500		ns
Total Gate Charge	Q_g	$V_{DS} = -36V, V_{GS} = -10V, I_D = -70A$		115		nC
Gate-to-Source Charge	Q_{gs}	$V_{DS} = -36V, V_{GS} = -10V, I_D = -70A$		20		nC
Gate-to-Drain "Miller" Charge	Q_{gd}	$V_{DS} = -36V, V_{GS} = -10V, I_D = -70A$		25		nC
Diode Forward Voltage	V_{SD}	$I_S = -70A, V_{GS} = 0V$		-1.0	-1.5	V

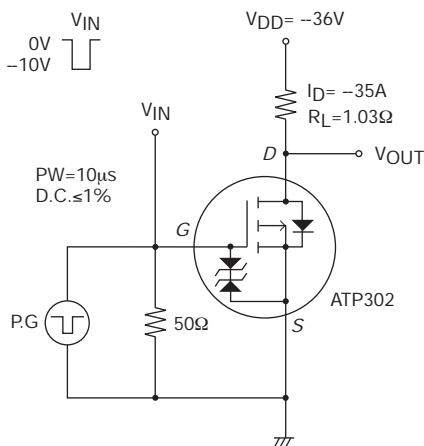
Package Dimensions

unit : mm (typ)

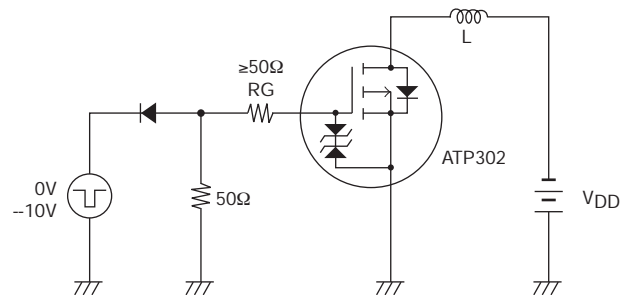
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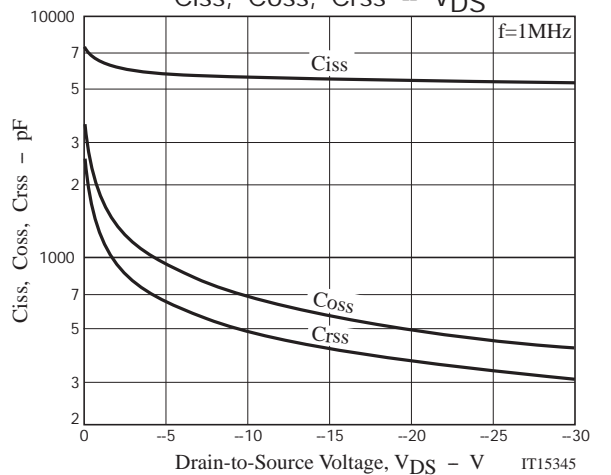
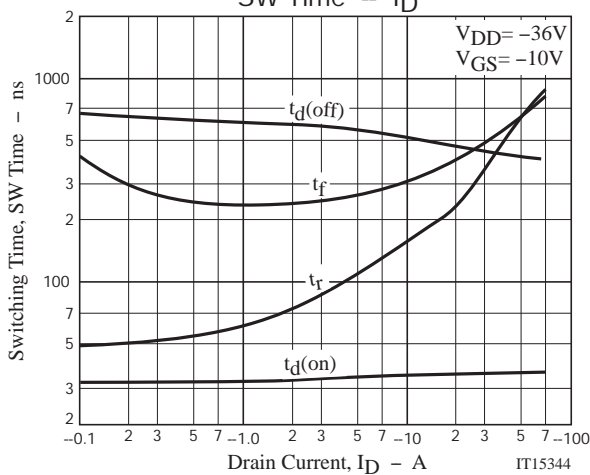
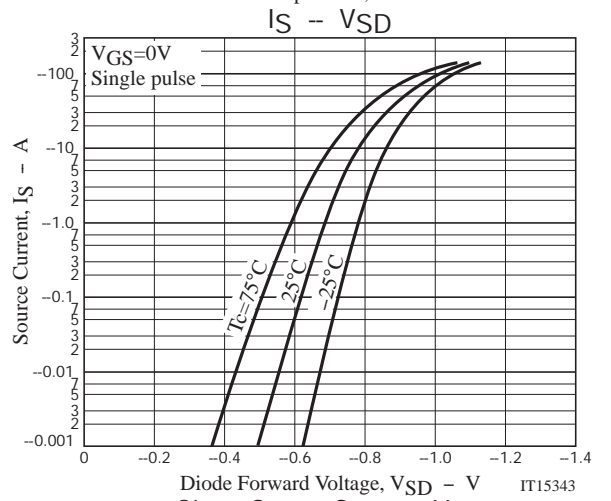
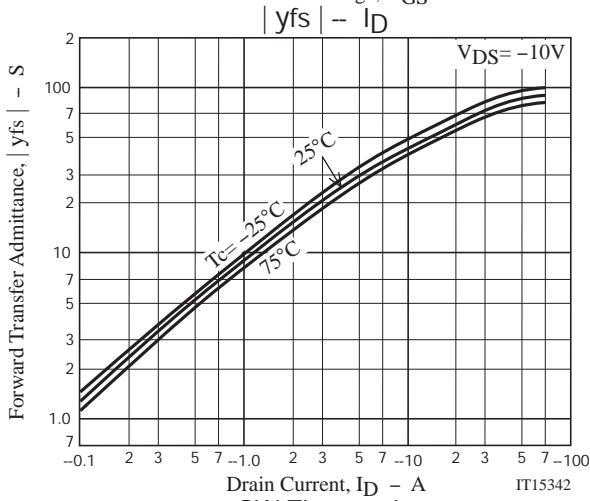
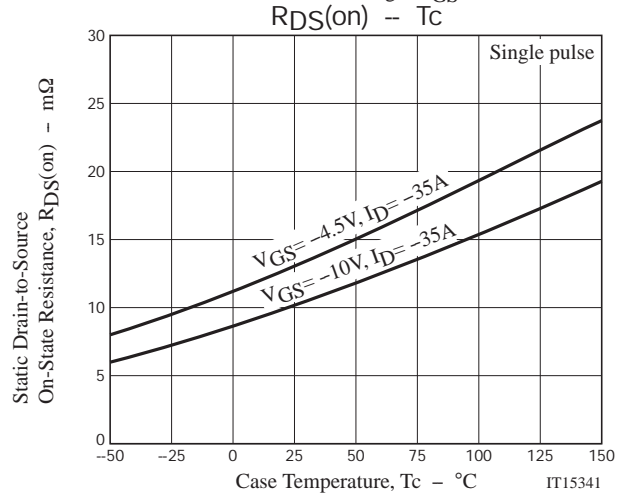
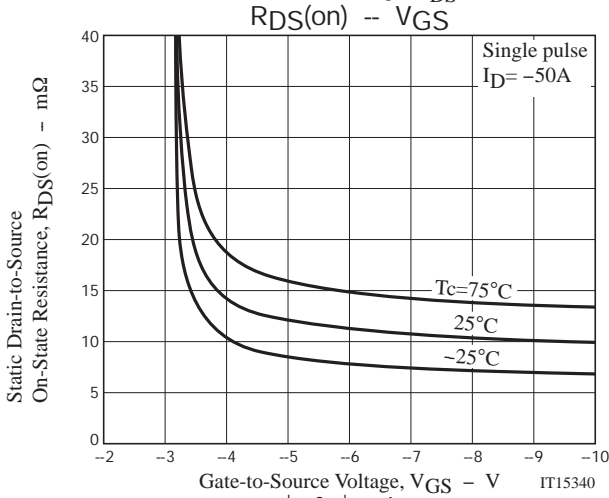
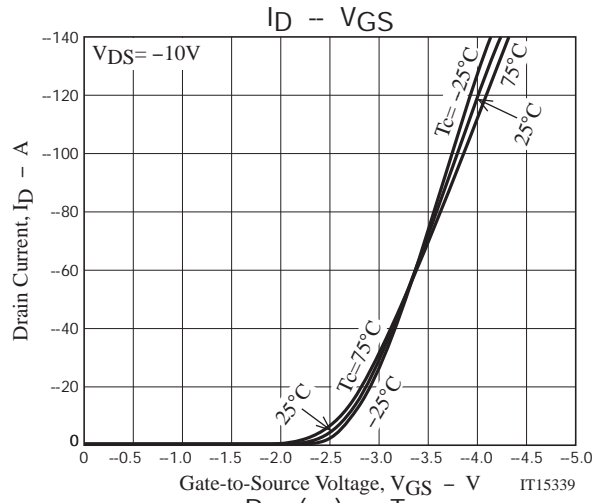
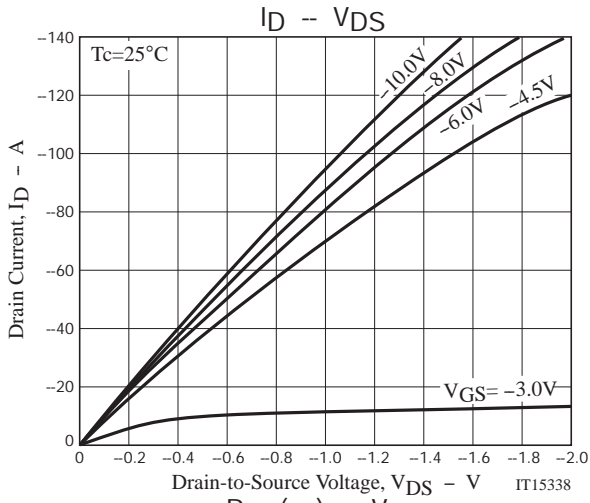


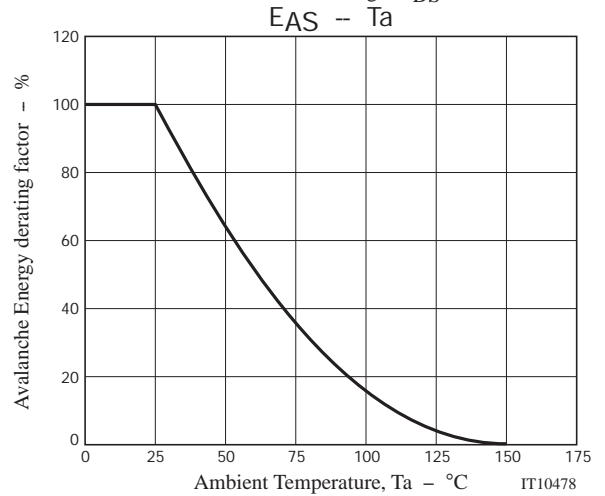
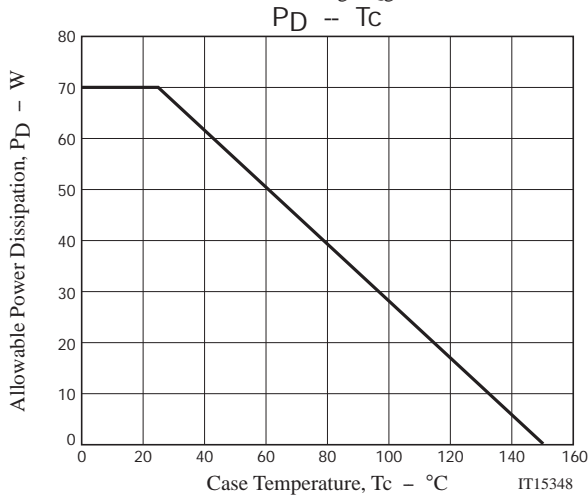
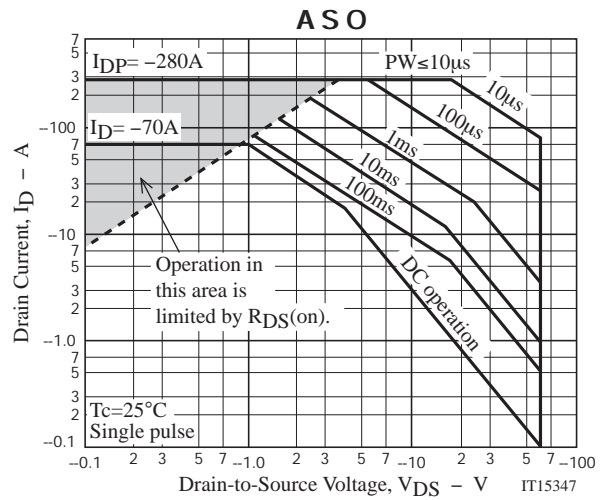
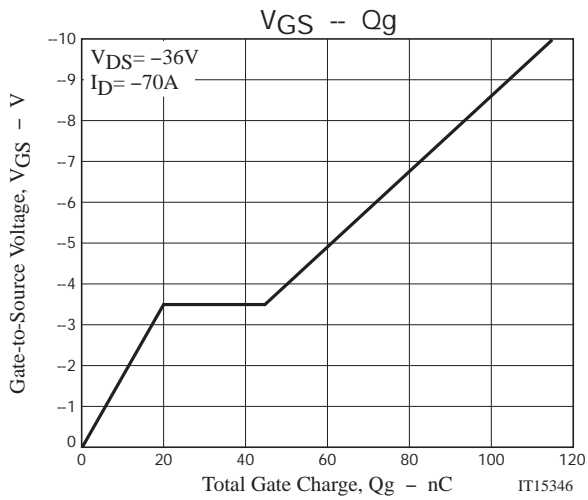
Switching Time Test Circuit



Avalanche Resistance Test Circuit







Note on usage : Since the ATP302 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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